Unit:mm

2SA1235A 2SA1602A 2SA1993

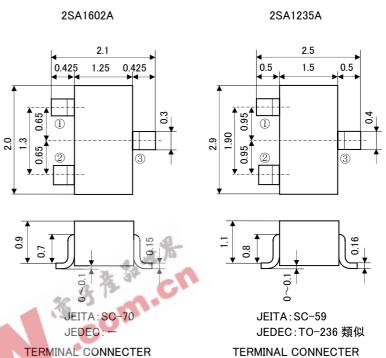
FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON PNP EPITAXIAL TYPE(Super mini type)

FEATURE

- Super mini package for easy mounting
- *Excellent linearity of DC forward gain
- •Small collector to emitter saturation voltage VCE(sat)=-0.3V max

APPLICATION

For Hybrid IC,small type machine low frequency voltageAmplify application



OUTLINE DRAWING

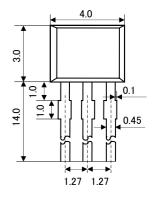
- 1:BASE
- ②: EMITTER
- 3: COLLECTOR

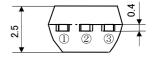


1:BASE

2:EMITTER

3: COLLECTOR





JEITA: —

JEDEC: -

TERMINAL CONNECTER

- $\textcircled{1} \colon \mathsf{EMITTER}$
- 2: COLLECTOR
- 3:BASE

2SA1235A 2SA1602A 2SA1993

FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON PNP EPITAXIAL TYPE(Super mini type)

MAXIMUM RATINGS(Ta=25°C)

Symbol	Parameter	Ratings			
	Parameter	2SA1235A	2SA1602A	2SA1993	Unit
V_{CBO}	Collector to Base voltage	-60	-60	-50	V
V_{EBO}	Emitter to Base voltage	-6			V
V _{CEO}	Collector to Emitter voltage	-50			٧
I c	Collector current	200			mA
Pc	Collector dissipation	200	200	450	mW
Tj	Junction temperature	+150			°C
Tstg	Storage temperature	−55 ~ +150			°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parame	Comple al	Test conditions		Limits			11
ter	Symbol			Min	Тур	Max	Unit
$V_{(BR)CEO}$	C to E break down voltage	I _C =-100 μ A, R _{BE} =∞		-50			٧
I _{CBO}	Collector cut off current	2SA1993	V_{CB} =-50V, I $_{E}$ =0			-0.1	μΑ
	Emitter cut off current	2SA1235A,2SA1602A	V _{CB} =-60V, I _E =0			-0.1	
I _{EBO}	DC forward current gain	V_{EB} =-6V, I $_{C}$ =0	7. 22			-0.1	μΑ
h _{FE} *	DC forward current gain	V_{CE} =-6V, I _C =-1mA	2 13 C	150		500	_
h _{FE}	C to E Saturation Vlotage	2SA1993	\/ - C\/ T - 0.1 - A	50			_
		2SA1235A,2SA1602A	$V_{CE}=-6V$, $I_{C}=-0.1$ mA	90			_
V _{CE(sat)}	Gain bandwidth product	I _c =-100mA, I _B =-10mA				-0.3	٧
f _T	Collector output capacitance	V _{CE} =-6V, I = =10mA			200		MHz
Cob	C to E break down voltage	V_{CB} =-6V, I_E =0,f=1MHz			4.0		pF
NF	Noise figure	$V_{CE} = -6V$, $I_{E} = 0.3$ mA, $f = 100$ H	z,RG=10kΩ			20	dB

*: It shows hFE classification in below table.

		E	F
hFE	2SA1235A		
	2SA1602A	150~300	250~500
	2SA1993		

2SA1235A 2SA1602A 2SA1993

FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON PNP EPITAXIAL TYPE(Super mini type)

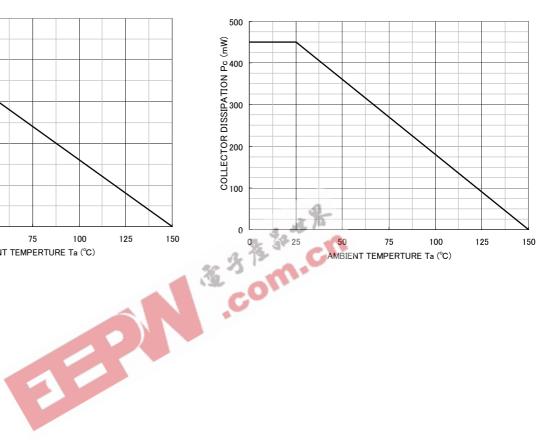
2SA1235A, 2SA1602

COLLECTOR DISSIPATION VS.AMBIENT TEMPERTURE

250 0 0 25 50 AMBIENT TEMPERTURE Ta (°C)

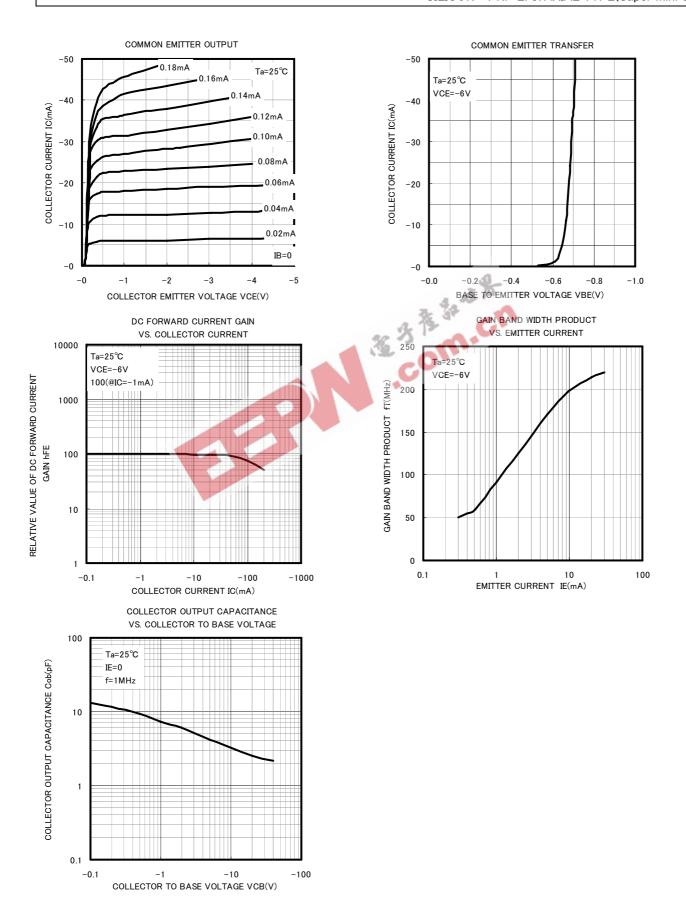
2SA1993

COLLECTOR DISSIPATION VS.AMBIENT TEMPERTURE



2SA1235A 2SA1602A 2SA1993

FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON PNP EPITAXIAL TYPE(Super mini type)





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